

isc Silicon PNP Power Transistor

2SA754

DESCRIPTION

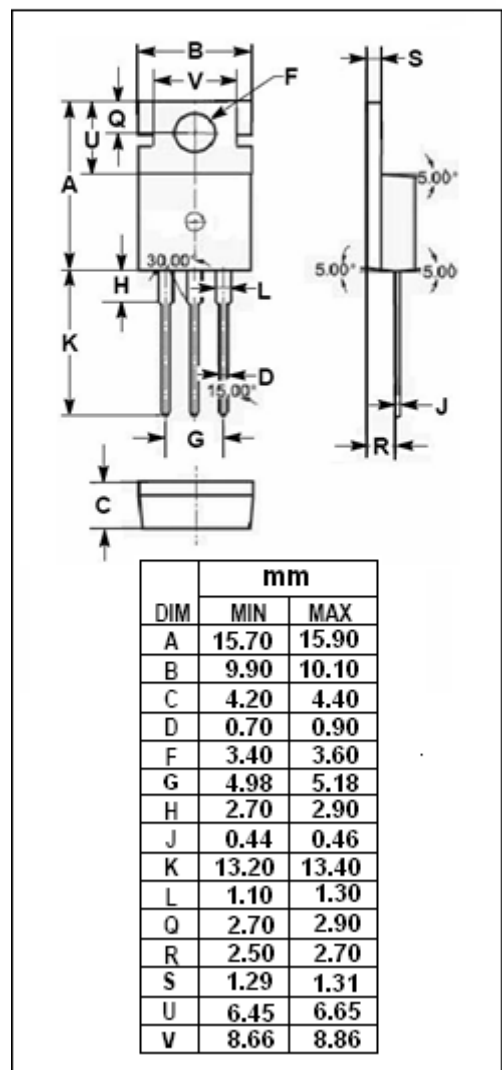
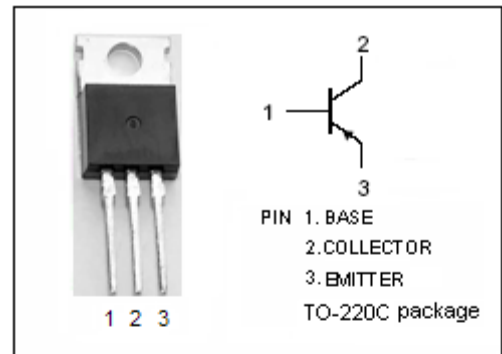
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -50V(\text{Min})$
- Low Collector Saturation Voltage-
: $V_{CE(sat)} = -1.3V(\text{Max.}) @ I_C = -1.5A$
- Good Linearity of h_{FE}

APPLICATIONS

- Designed for low frequency power amplifier applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-4	V
I_C	Collector Current-Continuous	-2	A
P_C	Total Power Dissipation@ $T_C=25^\circ\text{C}$	20	W
T_J	Junction Temperature	150	°C
T_{stg}	Storage Temperature Range	-55~150	°C



isc Silicon PNP Power Transistor**2SA754****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = -5\text{mA}; I_E = 0$	-50			V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -50\text{mA}; R_{BE} = \infty$	-50			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -5\text{mA}; I_C = 0$	-4			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -1.5\text{A}; I_B = -0.15\text{A}$			-1.3	V
$V_{BE(on)}$	Collector-Emitter On Voltage	$I_C = -1\text{A}; V_{CE} = -4\text{V}$			-1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -20\text{V}; I_E = 0$			-100	μA
h_{FE-1}	DC Current Gain	$I_C = -1\text{A}; V_{CE} = -4\text{V}$	35		200	
h_{FE-2}	DC Current Gain	$I_C = -0.1\text{A}; V_{CE} = -4\text{V}$	35			
f_T	Current-Gain—Bandwidth Product	$I_C = -0.5\text{A}; V_{CE} = -4\text{V}$		50		MHz

◆ **h_{FE-1} Classifications**

A	B	C
35-70	50-120	100-200